

45. (Withdrawn) The interconnect structure of claim 40, wherein the barrier layer is comprised of tantalum.

46. (Withdrawn) The interconnect structure of claim 40, wherein the conductive layer is comprised of copper.

### REMARKS

Applicants thanks Examiner for their detailed review of the application.

Applicant has amended claim 16 to include the limitation of claim 17, i.e. "the molar percentage of zeolite being in the range of one to fifty percent." As a result, applicant respectfully submits that claim 16 now further limits claim 15 and is in proper dependent form.

Examiner rejected claims 1, 3-4, 6, 8, 9, and 11-27 under 35 U.S.C. 102(e) as being anticipated by Ogihara et al. (U.S. publication 20040091419). Examiner states that applicant discloses, "any amount of liquid may be extracted to form a wet gel with different properties. For example a small amount of liquid...As another example some or almost all of the liquid." Applicant's amended claim 1 includes a first amount of liquid in the range of 5% to 95%, which is included within "any amount of liquid." Furthermore, applicant's amended claim 13 depends from claim 12, which further limits claim 1 by additional limitations of etching at least a via and a trench, forming a conductive material, and forming the wet gel - zeolite composite into an aerogel - zeolite composite, **after forming the conductive material.**

In contrast, Ogihara at col. 7 paragraph 0101 discloses:

The thin film thus prepared may be preferably heated for several minutes at 50 to 150 degrees C in a drying process (generally called a pre-bake in the semiconductor process) in an attempt to remove the solvent. A porous film is finally obtained.

Consequently, it is apparent that Ogihara does not contemplate extraction of some of the

liquid, i.e. in a range of 5% to 95% as in applicant's claim 1, to form a wet gel to withstand further processing as in applicant's claims 12-13, but rather removal of all of the solvent to create a final hardened porous film, which results in cracking and other problems applicant's disclosure is targeted at solving.

Therefore, Applicants respectfully submit that claim 1 and its dependent claims 3-16, and 18-28 are now in condition for allowance for the reasons stated above.

If there are any additional charges, please charge Deposit Account No. 50-0221. If a telephone interview would in any way expedite the prosecution of the present application, the Examiner is invited to contact David P. McAbee at (503) 712-4988.

Respectfully submitted,  
Intel Corporation

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